

LATERAL SEMICONDUCTOR STRUCTURE AND METHODS OF MANUFACTURE

Patent number: WO03036699
Publication date: 2003-05-01
Inventor: UDREA FLORIN (GB)
Applicant: CAMBRIDGE SEMICONDUCTOR LTD (GB); UDREA FLORIN (GB)
Classification:
- **International:** H01L21/20; H01L27/12; H01L21/762; H01L21/04; H01L29/861; H01L29/78; H01L29/739; H01L21/84
- **European:** H01L21/04D; H01L21/331G; H01L21/762D8; H01L21/84; H01L27/12B; H01L29/739C1; H01L29/78B1
Application number: WO2002GB04738 20021021
Priority number(s): US20010330506P 20011023

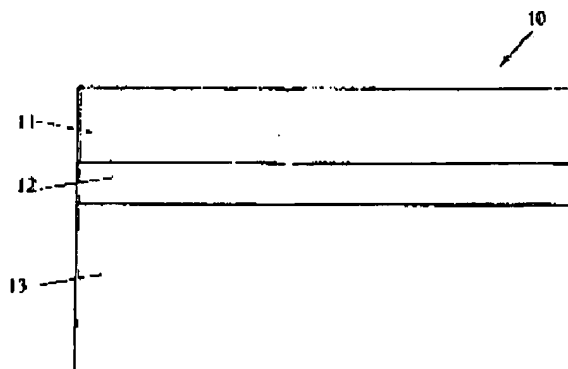
Also published as:
WO03036699 (A3)

Cited documents:
GB1114497
EP1081748
EP0905787
US2001016399
US6127243
more >>

[Report a data error here](#)

Abstract of WO03036699

A semiconductor structure (10) has a low bandgap semiconductor layer (11), a buried insulator layer (12) below the low bandgap semiconductor layer (11), and a wide bandgap semiconductor substrate (13). The low bandgap semiconductor layer (11) may be for example silicon, SiGe, GaAs or a heterojunction. The wide bandgap semiconductor layer (13) may be for example silicon carbide or diamond. A semiconductor device may be made by bonding a wide bandgap semiconductor wafer (13) via an insulator layer (12) to a low bandgap semiconductor wafer (11) and subsequently forming a semiconductor device in the low bandgap semiconductor wafer (11).



Data supplied from the esp@cenet database - Worldwide